

# PSMN017-30LL

N-channel DFN3333-8 30 V 17 mΩ logic level MOSFET

Rev. 4 — 12 December 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in DFN3333-8 package qualified to 150 °C. This product is designed and qualified for use in a wide range of industrial, communications and power supply equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources
- Small footprint for compact designs

### 1.3 Applications

- Battery protection
- Load switching
- DC-to-DC converters
- Power ORing

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 150\text{ °C}$	-	-	30	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	-	-	15	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	37	W
$T_j$	junction temperature		-55	-	150	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	-	20.5	25	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 100\text{ °C}$ ; see <a href="#">Figure 13</a>	-	-	23.4	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	-	15	17	mΩ

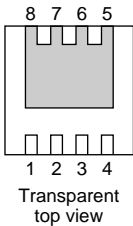
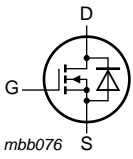


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $V_{DS} = 15\text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 17</a>	-	1.5	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}$ ; $I_D = 5\text{ A}$ ; $V_{DS} = 15\text{ V}$ ; see <a href="#">Figure 17</a> ; see <a href="#">Figure 14</a>	-	10	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $I_D = 35\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$	-	-	8	mJ

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>Transparent top view</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
5,6,7,8	D	mounting base; connected to drain		

**SOT873-1 (DFN3333-8)**

## 3. Ordering information

Table 3. Ordering information

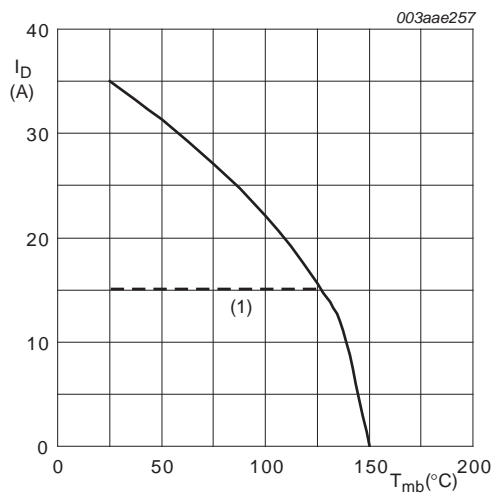
Type number	Package		Version
	Name	Description	
PSMN017-30LL	DFN3333-8	plastic thermal enhanced very thin small outline package; no leads; 8 terminals	SOT873-1

## 4. Limiting values

**Table 4. Limiting values**

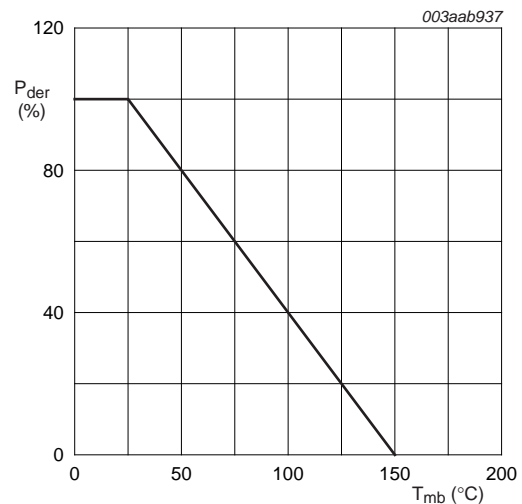
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$ ; $T_j \leq 150\text{ }^{\circ}\text{C}$	-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \leq 150\text{ }^{\circ}\text{C}$ ; $T_j \geq 25\text{ }^{\circ}\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 1</a>	-	15	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 1</a>	-	15	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 3</a>	-	140	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 2</a>	-	37	W
$T_{stg}$	storage temperature		-55	150	$^{\circ}\text{C}$
$T_j$	junction temperature		-55	150	$^{\circ}\text{C}$
$T_{sld(M)}$	peak soldering temperature		-	260	$^{\circ}\text{C}$
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	18	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$	-	140	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $I_D = 35\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$	-	8	mJ



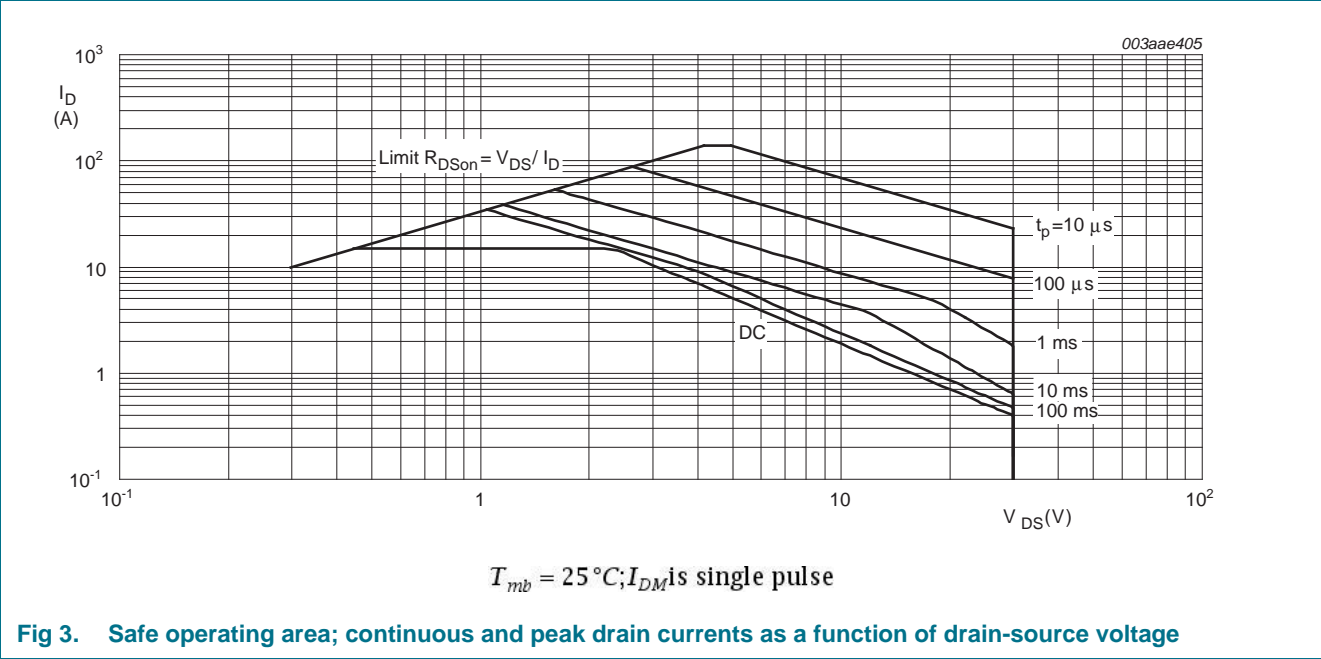
$V_{GS} \geq 10\text{ V}$ ; (1) Capped at 15 A due to wires.

**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of solder point temperature**



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	3.6	8.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	[1]	-	57	60	K/W

[1]  $R_{th(j-a)}$  is guaranteed by design and assumes that the device is mounted on a 40mm x 40mm x 70μm copper pad at 20°C ambient temperature. In practice  $R_{th(j-a)}$  will be determined by the customer's PCB characteristics

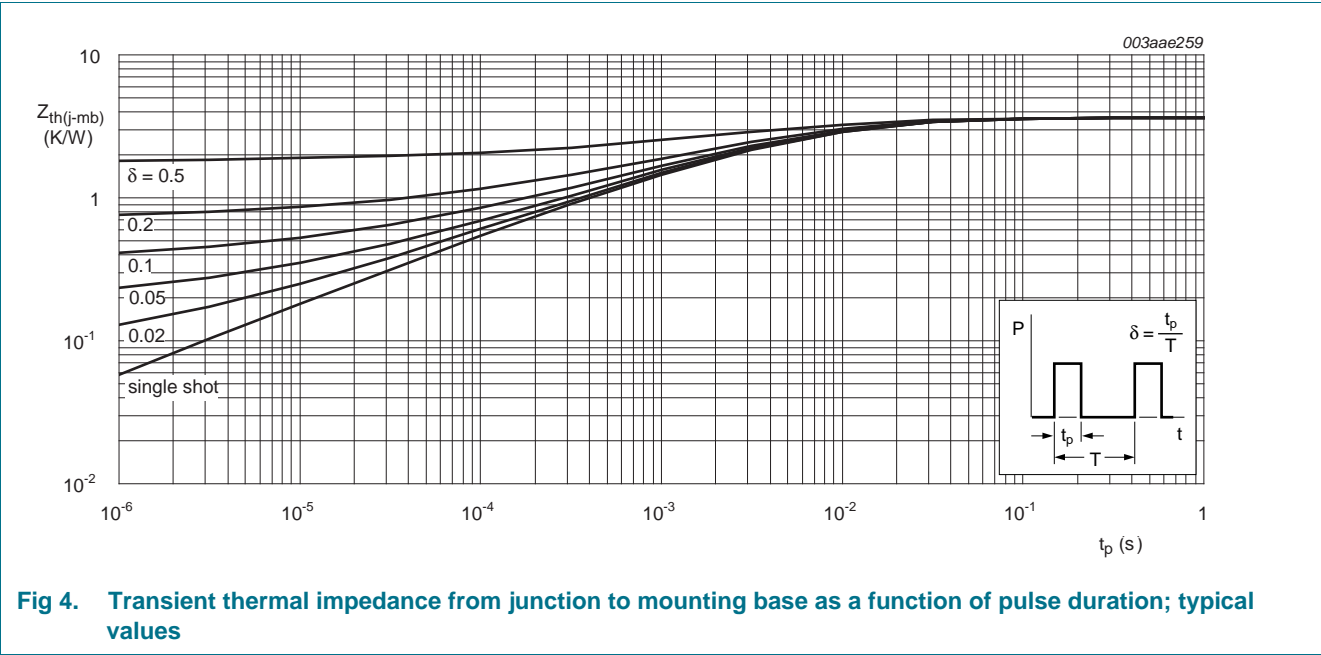


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

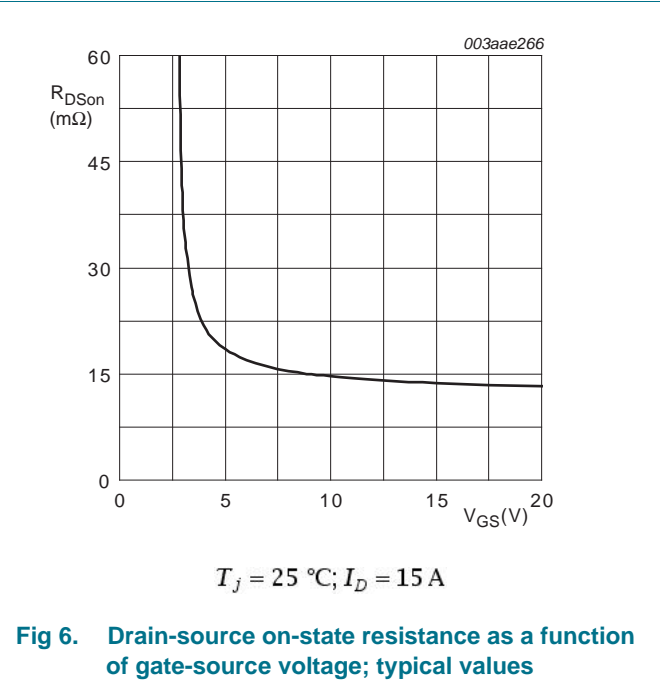
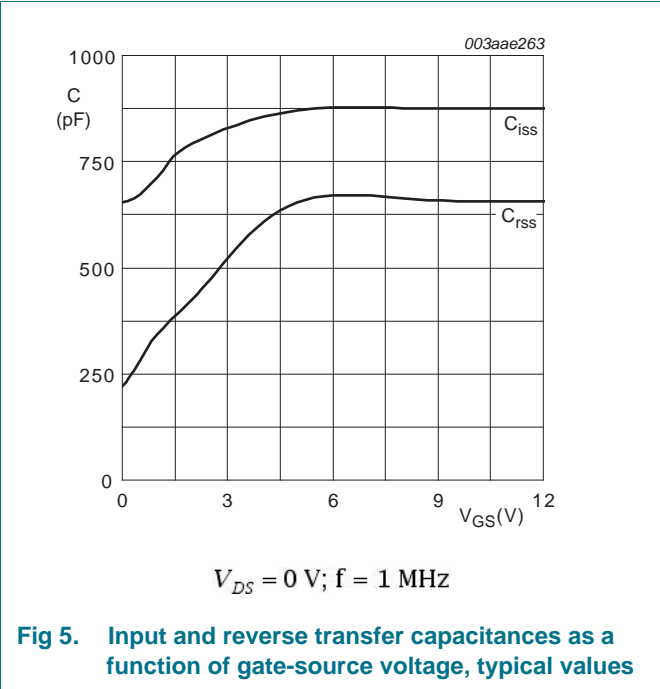
## 6. Characteristics

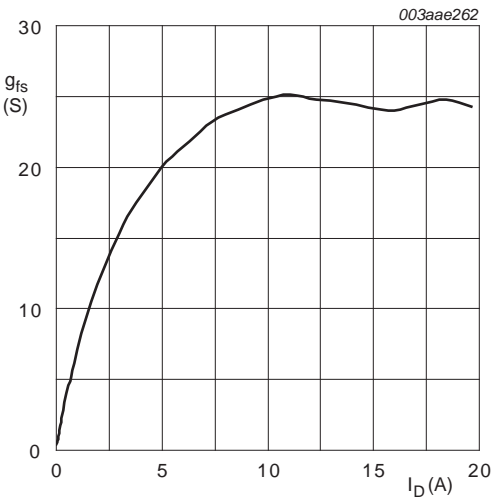
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a> ; see <a href="#">Figure 10</a>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	-	-	2.55	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	50	μA
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	5	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	5	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	20.5	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	-	23.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	27	30.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	15	17	mΩ
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	1.23	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 17</a>	-	10	-	nC
		$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <a href="#">Figure 17</a> ; see <a href="#">Figure 14</a>	-	5	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	9	-	nC
$Q_{GS}$	gate-source charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a>	-	1.8	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.8	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 17</a>	-	1.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 15 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 17</a>	-	2.7	-	V
$C_{iss}$	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	526	-	pF
$C_{oss}$	output capacitance	$T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	108	-	pF
$C_{rss}$	reverse transfer capacitance		-	53	-	pF

Table 6. Characteristics ...continued

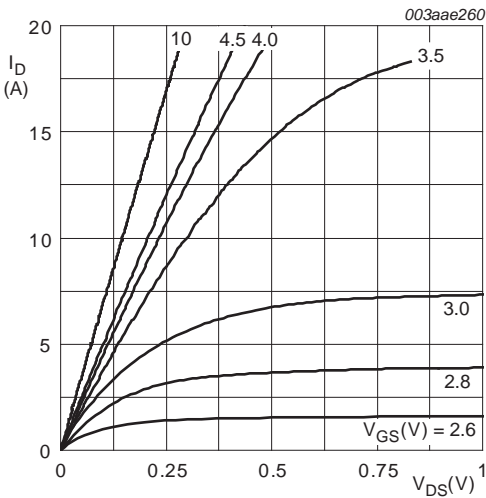
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; R <sub>L</sub> = 3 Ω; V <sub>GS</sub> = 4.5 V; R <sub>G(ext)</sub> = 4.7 Ω; T <sub>j</sub> = 25 °C	-	13	-	ns
t <sub>r</sub>	rise time		-	12	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	18.3	-	ns
t <sub>f</sub>	fall time		-	5.8	-	ns
Source-drain diode						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <a href="#">Figure 16</a>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 5 A; dI <sub>S</sub> /dt = 100 A/μs; V <sub>GS</sub> = 0 V;	-	10	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V	-	17	-	nC





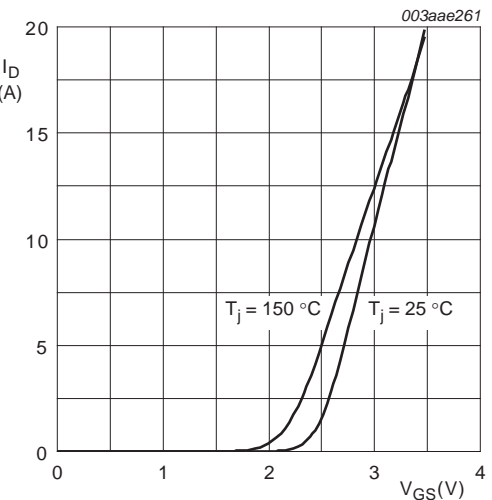
$T_j = 25\text{ °C}; V_{DS} = 10\text{ V}$

Fig 7. Forward transconductance as a function of drain current; typical values



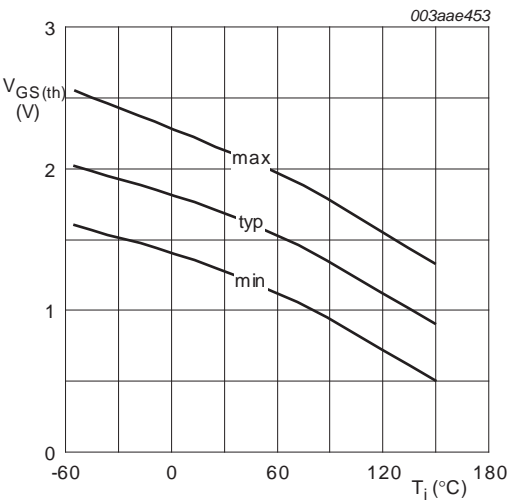
$T_j = 25\text{ °C}$

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



$V_{DS} > I_D \times R_{DSon}$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

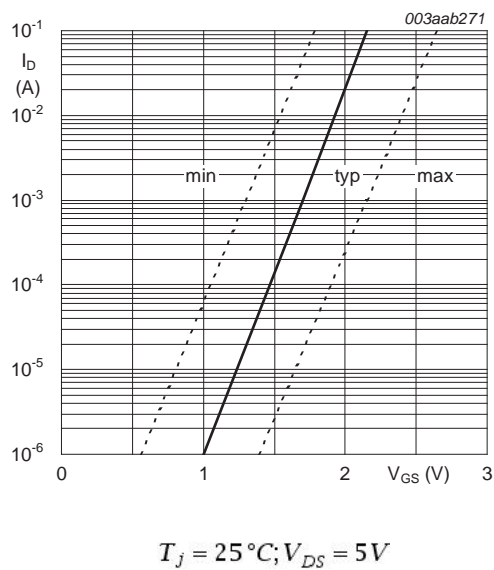


Fig 11. Sub-threshold drain current as a function of gate-source voltage

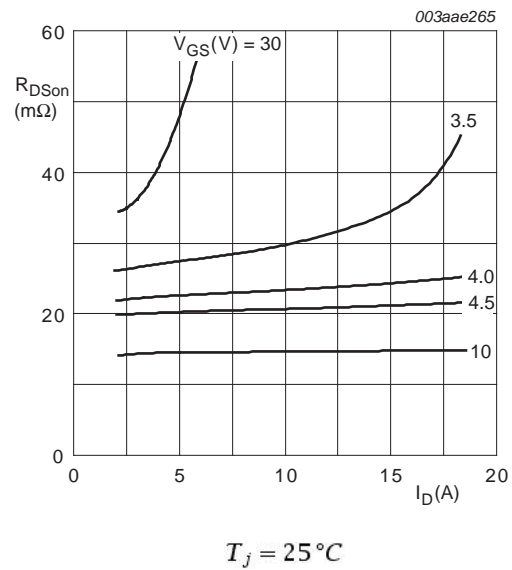


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

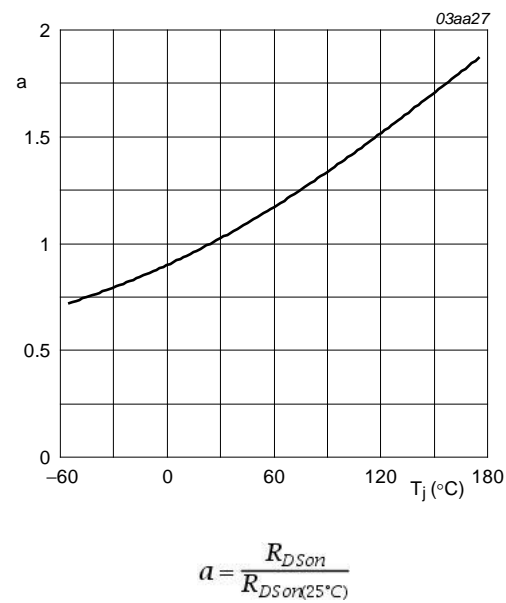


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

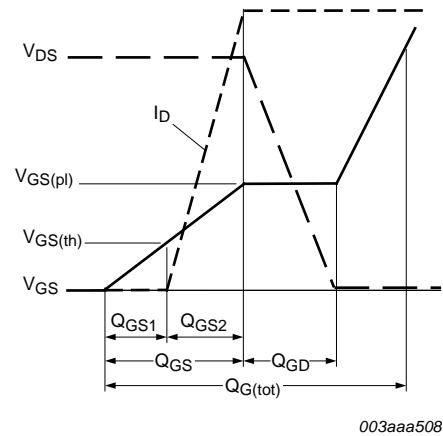


Fig 14. Gate charge waveform definitions

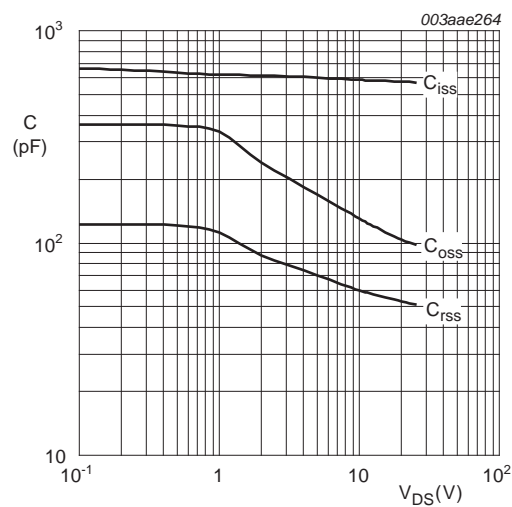


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

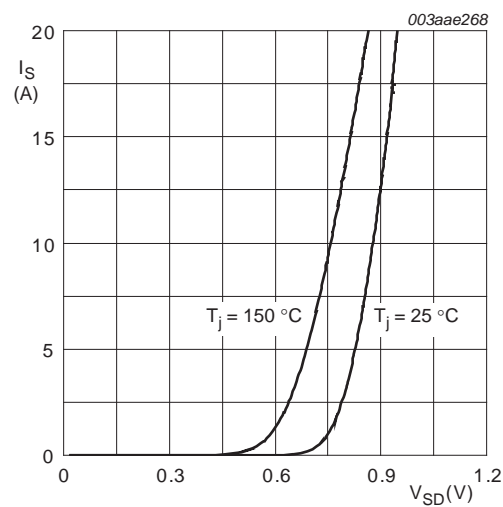


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

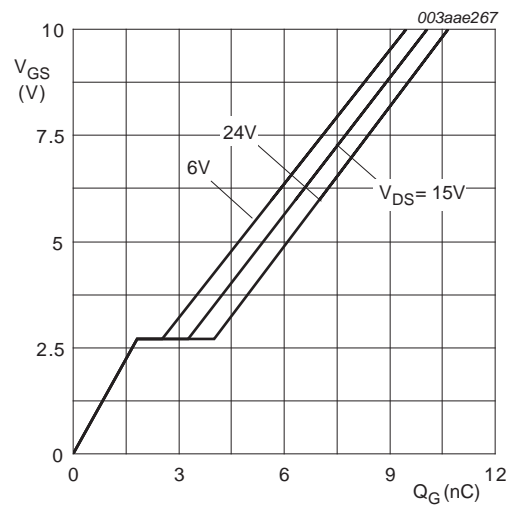


Fig 17. Gate-source voltage as a function of gate charge; typical values

7. Package outline

DFN3333-8: plastic thermal enhanced very thin small outline package; no leads;  
8 terminals; body 3.3 x 3.3 x 1.0 mm

SOT873-1

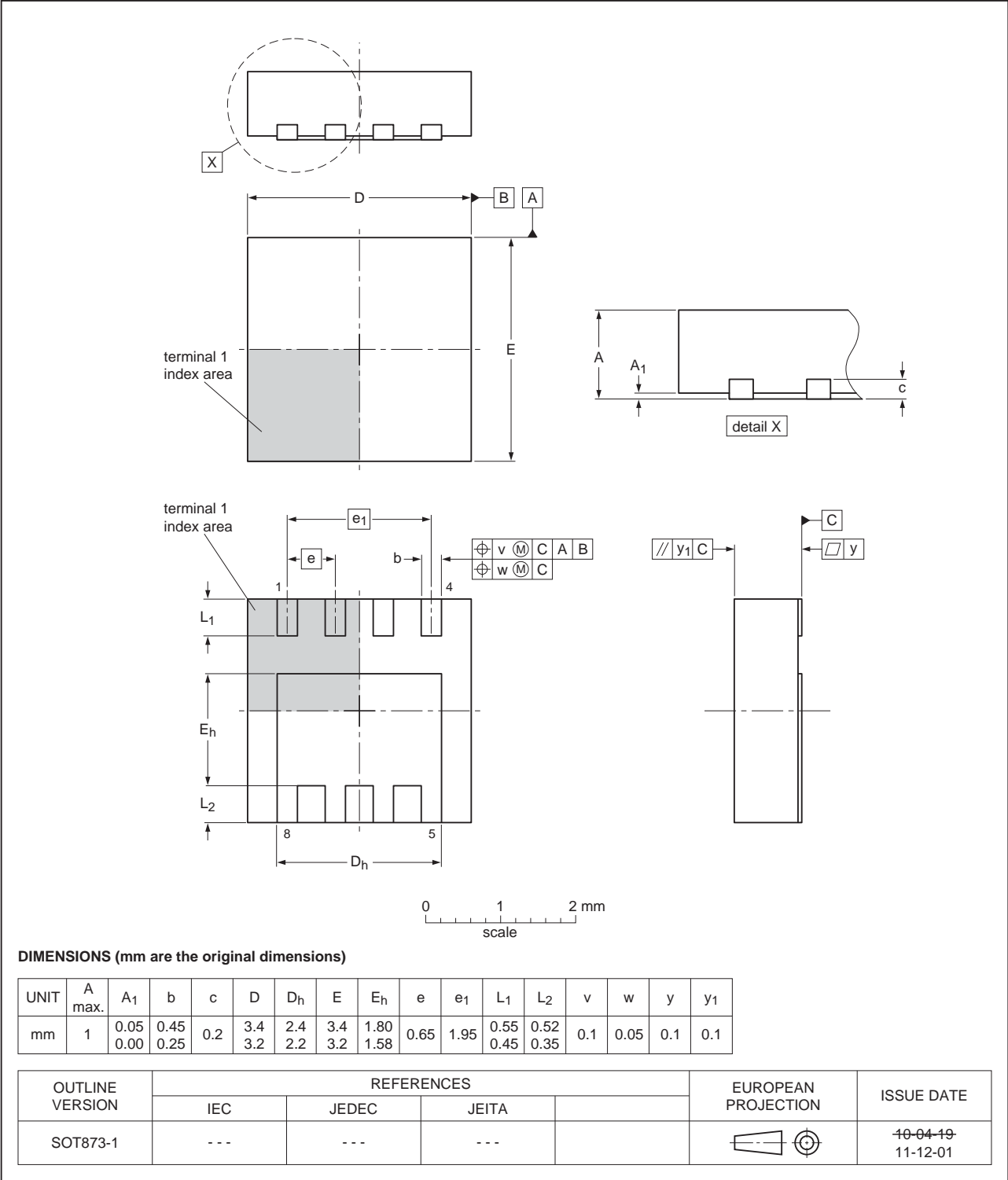


Fig 18. Package outline SOT873-1 (DFN3333-8)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN017-30LL v.4	20111212	Product data sheet	-	PSMN017-30LL v.3
Modifications:	• Various changes to content.			
PSMN017-30LL v.3	20100707	Product data sheet	-	PSMN017-30LL v.2

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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Date of release: 12 December 2011

Document identifier: PSMN017-30LL